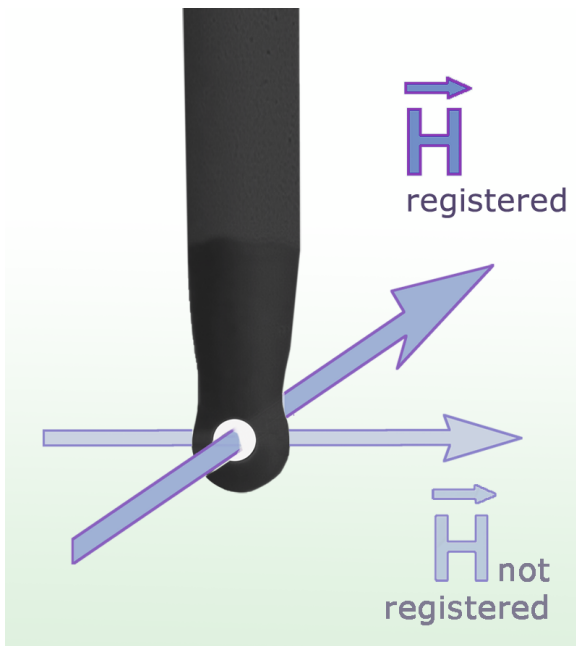


RF-R 3-2

磁场探头 (30MHz-3GHz)



Short description

RF-R 3-2型近场探头，分辨率高，用于直接检测电子组装件上的射频磁场，例如引脚区域、集成电路外壳、导线、旁路电容器和电磁兼容性（EMC）元件等的磁场。

The RF-R 3-2 is a passive near-field probe. It has the same basic construction as the RF-R 50-1 and RF-R 500-1 probes. However, the resolution of RF-R 3-2 is much higher. The H-field probe is designed to be used very close to the components and where high magnetic field strength occurs. It is not suitable for measurements from great distances, which can be done using the RF-R 400-1 and RF-R 50-1 probes. The near-field probe is small and handy. It has a current attenuating sheath and its upper side is electrically shielded. It can be connected to a spectrum analyzer or an oscilloscope with a 50 Ω input. The H-field probe does not have an internal terminating resistance of 50 Ω .

Technical parameters

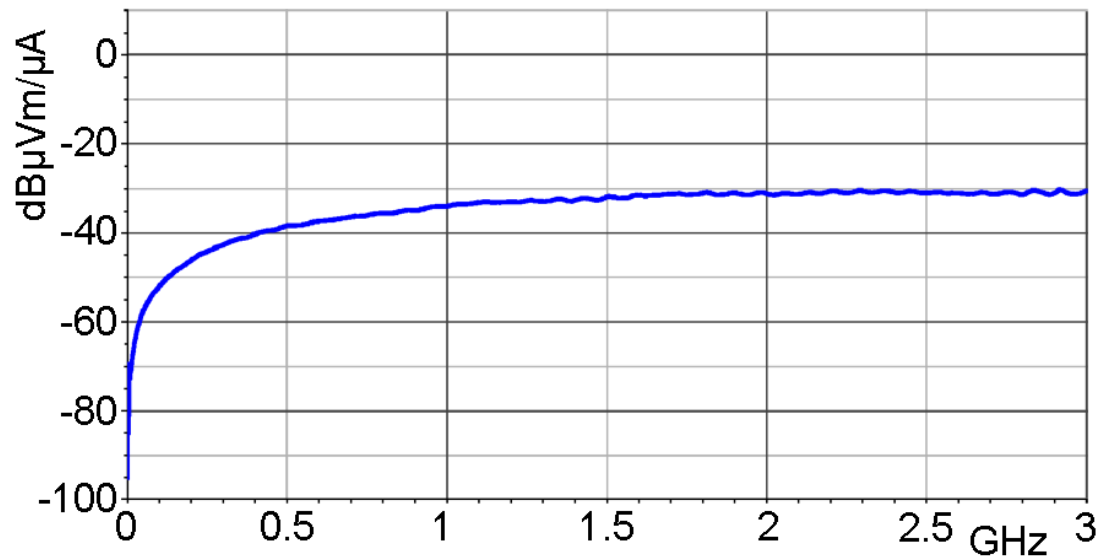
频率范围	30 MHz ... 3 GHz
分辨率	≈ 1 mm
探头尺寸	$\varnothing \approx 3$ mm
输出接口	SMB, male, jack
重量	15 g

RF-R 3-2

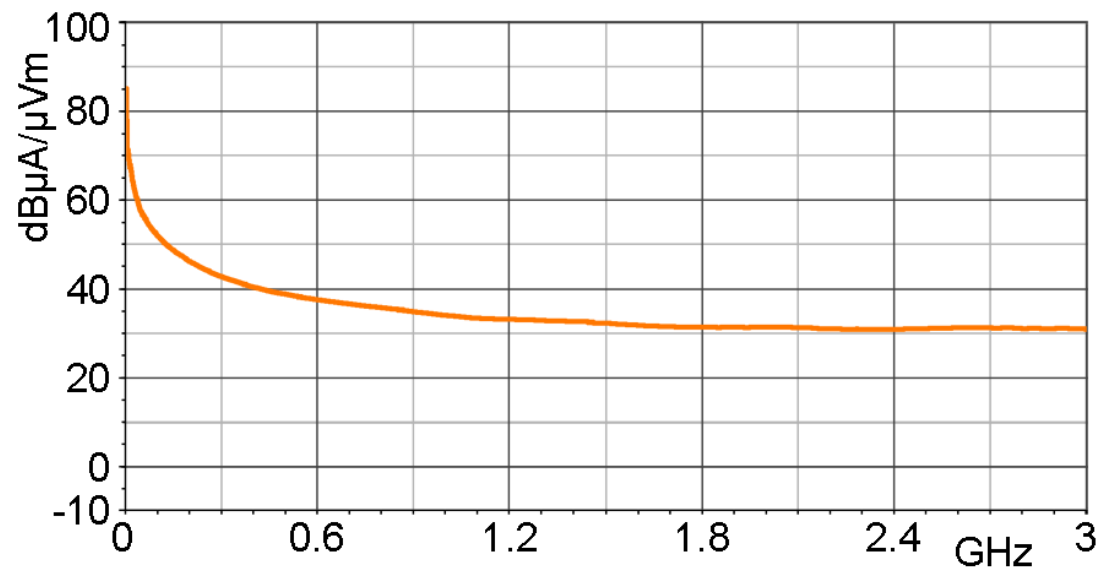
磁场探头 (30MHz-3GHz)

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频率特性 [dB μ V] / [dB μ A/m]



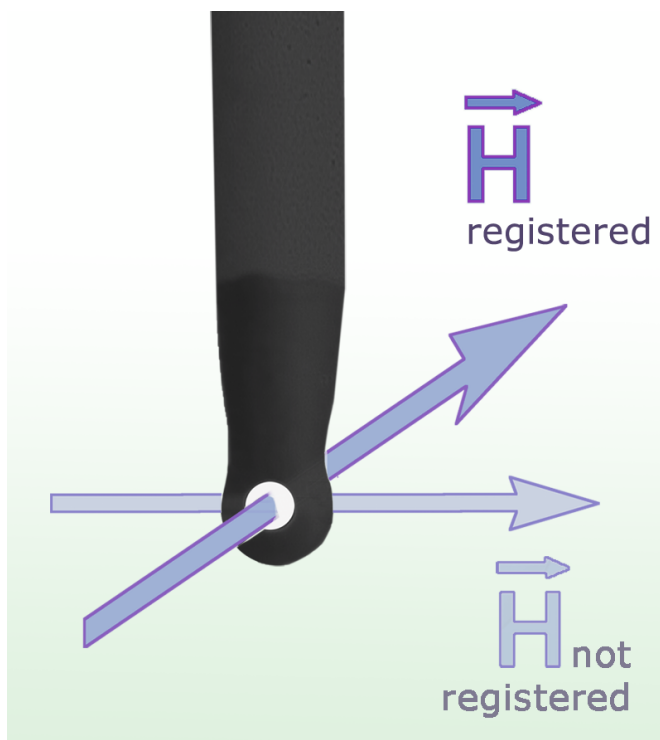
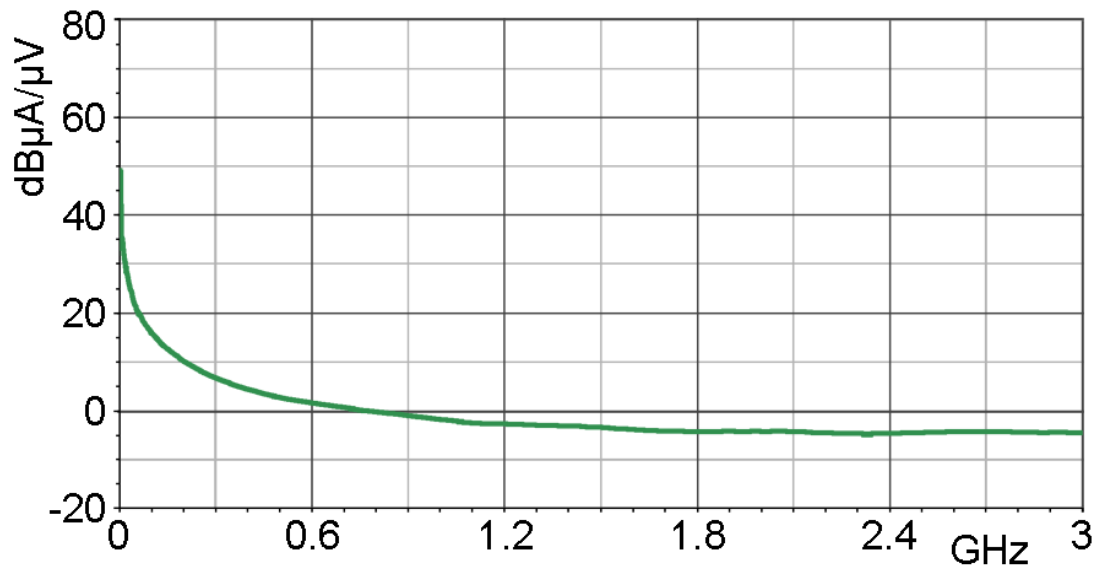
磁场校正曲线 [dB μ A/m] / [dB μ V]



RF-R 3-2

磁场探头 (30MHz-3GHz)

电流校正曲线 [dB μ A] / [dB μ V]



RF-R 3-2

磁场探头 (30MHz-3GHz)

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Probe head

